

IEEE EDS Mini-Colloquium on “Non-Conventional Devices and Technologies”

An IEEE EDS Mini-Colloquium on „Non-conventional Devices and Technologies“ will take place in the time frame of the “Joint Spring MOS-AK Workshop and Symposium on Schottky Barrier MOS (SB-MOS) devices”. The MQ is held on March 18th 2020 at the Technische Hochschule Mittelhessen – University of Applied Sciences, Germany.

IEEE Distinguished Lecturers of the IEEE EDS Mini-Colloquium:

Prof. Joachim Burghartz (Universität Stuttgart, IMS Chips, Germany)
 Dr. Wlodek Grabinski (MOS-AK Association, Switzerland)
 Dr. Frank Schwierz (TU Illmenau, Germany)
 Prof. Benjamin Iniguez (Universitat Rovira i Virgili, Spain)
 Prof. Tibor Grasser (TU Vienna, Austria)

Attendees are welcome to participate the joint R&D event. Further information is present at

Symposium of SBMOS

<https://ssbmoss.blogspot.com>


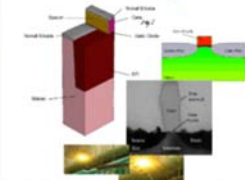
and

MOS-AK

http://www.mos-ak.org/giessen_2020

To register for the MOS-AK, Symposium of SB-MOS and IEEE EDS MQ use the vTools of IEEE with following link:

<https://meetings.vtools.ieee.org/m/205571>

<p>MOS-AK</p> <p>MOS-AK Meetings are organized with aims to strengthen a network and discussion forum among experts in the field, enhance open platform for information exchange related to compact/Spice modeling and Verilog-A standardization, bring people in the compact modeling field together, as well as obtain feedback from technology developers, circuit designers, and CAD tool vendors. The topics cover all important aspects of compact model development, implementation, deployment and standardization within the main theme - frontiers of the compact modeling for nm-scale MEMS/NEMS designs, CMOS/SoI and HEMT IC simulation.</p> <p>Topics to be covered include the following:</p> <ul style="list-style-type: none"> - Advances in semiconductor technologies and processing - Compact Modeling (CM) of the electron devices - Verilog-A language for CM standardization - New CM techniques and extraction software - Open Source FOSS TCAD/EDA modeling and simulation - CM of passive, active, sensors and actuators - Emerging Devices, CMOS and SOI-based memory cells - Microwave, mmW, RF device modeling, high voltage device modeling - Microsystems, SoC, IP modeling - Device level modeling for BioMed applications - Nanoscale semiconductor devices/circuits and its reliability/aging - Technology R&D, DfV, DfT and IC Design - Foundry/Fabless Interface Strategies <p>Symposium on Schottky Barrier MOS Devices</p> <p>The symposium goal is to combine the activities of an enthusiastic group of Schottky barrier researchers worldwide. The topics cover all important aspects of potential applications, simulation and modeling, processing and implementation for CMOS/SoI technologies, Quantum technologies and approaches for neuromorphic applications.</p> <p>The content will be beneficial for anyone who needs to learn the opportunities and challenges of this technology since the first introduction by Walter Schottky in the 1930s. New aspects and future proposals to make the Schottky barrier into the main stream are welcome.</p> <p>Tentative Speakers</p> <ul style="list-style-type: none"> - Prof. M. Lemme (RWTH Aachen, AMO GmbH, Germany) - Prof. W. Weber (TU Vienna, Austria) - Prof. D. Flandre (UC Louvain, Belgium) - Dr. L. Cahret (C2N, France) - Dr. M. Schwierz (Robert Bosch GmbH, Germany) 	<p>IEEE Mini-Colloquium (MQ)</p> <p>“Non-Conventional Devices and Technologies”</p> <p>The MQ will provide an open forum for education and discussion of non-conventional trends in the evolution of semiconductor electronics. Lectures will cover basics of 2D materials and introduce promising post-CMOS devices (2D transistors, 2D sensors, 2D optoelectronics) as well as flexible electronics based on organic/AOS semiconductors or thinned silicon.</p> <p>IEEE Distinguished Lecturers:</p> <ul style="list-style-type: none"> - Prof. J. Burghartz (Uni Stuttgart, IMS Chips, Germany) - Dr. W. Grabinski (MOS-AK Association, Switzerland) - Dr. F. Schwierz (TU Illmenau, Germany) - Prof. B. Iniguez (Universitat Rovira i Virgili, Spain) - Prof. T. Grasser (TU Vienna, Austria) <p>The Venue</p> <p>The joint workshop is held at the Competence Center for Nanotechnology and Photonics, TH Mittelhessen - Univ. of Applied Sciences, Giessen, Germany.</p> <p>Giessen. is a small city in the German federal state of Hessen. The population is approximately 86000, with roughly 24000 university students. The name comes from Gietzen, as it was first referred to in 1197, which refers to the position of the town between several rivers, lakes and streams. The largest river in Giessen is the Lahn, which divides the town in two parts (west and east), roughly 65 kilometers (40 miles) north of Frankfurt am Main.</p> <p>Travel Arrangement</p> <p>Air: Giessen is served by Frankfurt Main Airport (FRA), located 70 km south of the city center. From FRA various connections by railway are available.</p> <p>Rail: Direct railway connections from Frankfurt main station are available. Connection from Frankfurt airport to main station are available by metro and/or intercity connections. Airport to Giessen connection takes approximately 1 hour. Main station to Giessen approximately 50 minutes.</p> <p>Road: Giessen can be easily reached by road from major cities in Europe by A5, A45 and A485.</p> <p>Organized by:</p> <p>Prof. Alexander Kloeß, Nanop, Germany; Dr. Wlodek Grabinski, Robert Bosch GmbH, Germany; Dr. Wlodek Grabinski, MOS-AK Association, Berlin/and; Dr. Laura Carlet, C2N, France; Paris, France</p>	<p>The Event</p> <p>MOS-AK Spring Workshop 17. March 2020 IEEE Mini-Colloquium 18. March 2020 Symposium Schottky Barrier MOS Devices 18. March 2020</p> <p>On March 17th a conference dinner is organized and included in the registration.</p> <p>Abstract and Deadlines</p> <p>Intended authors should send an abstract (max. 300 words) to the email (alexander.kloes@isi.thm.de) with the event of interest and note the following deadlines:</p> <p>Receipt of abstract 24. February 2020 Notification of acceptance 29. February 2020 Registration deadline 06. March 2020</p> <p>Best papers will be selected for a special Solid-State-Electronics (SSE) compact modeling issue of MOS-AK activities.</p> <p>Registration & Price Information</p> <p>The joint spring MOS-AK workshop & Symposium on Schottky Barrier MOS devices is for free, no fees required. The attendance does not include accommodation and transport.</p> <p>The registration takes place by the vTools of IEEE. The following link is provided: https://meetings.vtools.ieee.org/m/205571</p> <p>WWW</p> <p>Further information are present under http://www.mos-ak.org/giessen_2020/ and/or http://ssbmoss.blogspot.com</p> 	<p style="text-align: right;">Students welcome! Workshop for free!</p> <p style="text-align: center;">ANNOUNCEMENT 2nd CALL FOR PAPERS Joint Spring MOS-AK Workshop & Symposium on Schottky Barrier MOS Devices 2020 IEEE MQ “Non-Conventional Devices and Technologies”</p>  <p>THM NanoP, IEEE, youngprofessionals GERMANY, Admos, ELECTRON JOURNAL SOCIETY</p> <p style="text-align: center;">Giessen, Germany, 17th - 18th March 2020</p>
---	--	--	--